

Masahiko Hasumi

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Dimensionality of the Superconductivity in YBa ₂ Cu ₃ O _{7-δ} . Journal of the Physical Society of Japan, 1988, 57, 1554-1557.	1.6	34
2	Antiferromagnetic Transition in Y ₂ BaCuO ₅ . Japanese Journal of Applied Physics, 1987, 26, L2018-L2020.	1.5	33
3	Mechanical Stacking Multi Junction Solar Cells Using Transparent Conductive Adhesive. Energy Procedia, 2014, 60, 116-122.	1.8	30
4	Magnetic Susceptibility of YBa ₂ Cu ₃ O _{7-x} with Various Oxygen Deficiency. Journal of the Physical Society of Japan, 1988, 57, 2272-2275.	1.6	29
5	Minority Carrier Lifetime Measurements by Photoinduced Carrier Microwave Absorption Method. Japanese Journal of Applied Physics, 2011, 50, 03CA02.	1.5	22
6	Multi Junction Solar Cells Stacked with Transparent and Conductive Adhesive. Japanese Journal of Applied Physics, 2011, 50, 052301.	1.5	21
7	Low-Temperature Fabrication of Ultrathin ZrO ₂ /Si Structure Using Metal Deposition Followed by Oxygen Annealing. Japanese Journal of Applied Physics, 2005, 44, 5-7.	1.5	20
8	Multi Junction Solar Cells Stacked with Transparent and Conductive Adhesive. Japanese Journal of Applied Physics, 2011, 50, 052301.	1.5	19
9	HfO ₂ /Si and HfSiO/Si Structures Fabricated by Oxidation of Metal Thin Films. Japanese Journal of Applied Physics, 2009, 48, 05DA01.	1.5	15
10	Low-Temperature Electron Spin Susceptibility in YBa ₂ Cu ₃ O _{7-x} . Journal of the Physical Society of Japan, 1988, 57, 3301-3304.	1.6	13
11	Crystalline Silicon Solar Cells with Two Different Metals. Japanese Journal of Applied Physics, 2010, 49, 110205.	1.5	13
12	Minority Carrier Lifetime Measurements by Photoinduced Carrier Microwave Absorption Method. Japanese Journal of Applied Physics, 2011, 50, 03CA02.	1.5	11
13	Investigation of Silicon Surface Passivation by Microwave Annealing Using Multiple-Wavelength Light-Induced Carrier Lifetime Measurement. Japanese Journal of Applied Physics, 2013, 52, 011801.	1.5	10
14	Activation of silicon implanted with phosphorus and boron atoms by microwave annealing with carbon powder as a heat source. Japanese Journal of Applied Physics, 2014, 53, 05FV05.	1.5	9
15	Characterization of Plasma-Irradiated SiO ₂ /Si Interface Properties by Photoinduced-Carrier Microwave Absorption Method. Japanese Journal of Applied Physics, 2011, 50, 03CA03.	1.5	8
16	Heat treatment of amorphous silicon p-i-n solar cells with high-pressure H ₂ O vapor. Journal of Non-Crystalline Solids, 2012, 358, 2285-2288.	3.1	7
17	Photoinduced carrier annihilation in silicon pn junction. Japanese Journal of Applied Physics, 2015, 54, 081302.	1.5	7
18	Activation of dopant in silicon by ion implantation under heating sample at 200°C. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	7

#	ARTICLE	IF	CITATIONS
19	Photo induced minority carrier annihilation at crystalline silicon surface in metal oxide semiconductor structure. Japanese Journal of Applied Physics, 2014, 53, 031301.	1.5	6
20	Investigation of conductivity of adhesive layer including indium tin oxide particles for multi-junction solar cells. Applied Physics A: Materials Science and Processing, 2014, 116, 2113-2118.	2.3	6
21	Indium-gallium-zinc-oxide layer used to increase light transmittance efficiency of adhesive layer for stacked-type multijunction solar cells. Japanese Journal of Applied Physics, 2015, 54, 112301.	1.5	6
22	Carbon Heating Tube Used for Rapid Heating System. IEEE Access, 2019, 7, 23798-23805.	4.2	6
23	Surface Passivation of Crystalline Silicon by Combination of Amorphous Silicon Deposition with High-Pressure H ₂ O Vapor Heat Treatment. Japanese Journal of Applied Physics, 2012, 51, 03CA06.	1.5	5
24	Characterization of the High-Tc Superconductors Rare-Earth-Ba-Cu Oxides Resistivity, Susceptibility and Structure. Japanese Journal of Applied Physics, 1987, 26, 1033.	1.5	4
25	Crystallization and activation of silicon by microwave rapid annealing. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	4
26	Critical Field Anisotropy in κ -2K-Superconducting State of Organic Superconductor $\hat{\Gamma}^2$ -(BEDT-TTF) ₂ I ₃ . Journal of the Physical Society of Japan, 1989, 58, 3477-3480.	1.6	4
27	Fabrication of High-k/Si Structure Using Metal Deposition Followed by Oxidation. ECS Transactions, 2009, 16, 139-145.	0.5	3
28	Crystallization of Amorphous Silicon Thin Films by Microwave Heating. Materials Research Society Symposia Proceedings, 2014, 1666, 115.	0.1	3
29	Passivation of silicon surfaces by heat treatment in liquid water at 110 Å°C. Japanese Journal of Applied Physics, 2015, 54, 106503.	1.5	3
30	Characterization of Plasma-Irradiated SiO ₂ /Si Interface Properties by Photoinduced-Carrier Microwave Absorption Method. Japanese Journal of Applied Physics, 2011, 50, 03CA03.	1.5	3
31	Thermal Stability of HfO ₂ Films Fabricated by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 31-34.	1.5	2
32	Multi junction solar cells using band-gap induced cascaded light absorption. Japanese Journal of Applied Physics, 2014, 53, 05FV07.	1.5	2
33	Laser annealing of plasma-damaged silicon surface. Applied Surface Science, 2015, 336, 73-78.	6.1	2
34	Indium gallium zinc oxide layer used to decrease optical reflection loss at intermediate adhesive region for fabricating mechanical stacked multijunction solar cells. Japanese Journal of Applied Physics, 2017, 56, 012602.	1.5	2
35	Experimental studies of three superconducting states in the organic superconductor $\hat{\Gamma}^2$ -(BEDT-TTF) ₂ I ₃ . Physica C: Superconductivity and Its Applications, 1991, 185-189, 2675-2676.	1.2	1
36	Infrared semiconductor laser irradiation used for crystallization of silicon thin films. Journal of Non-Crystalline Solids, 2012, 358, 2162-2165.	3.1	1

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37	Minority Carrier Annihilation at Crystalline Silicon Interface in Metal Oxide Semiconductor Structure. Materials Research Society Symposia Proceedings, 2014, 1666, 18.	0.1	1
38	Passivation of Silicon Surfaces by Treatment in Water at 110°C. Materials Research Society Symposia Proceedings, 2015, 1770, 37-42.	0.1	1
39	Heat treatment in 110°C liquid water used for passivating silicon surfaces. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	1
40	Surface Passivation of Crystalline Silicon by Combination of Amorphous Silicon Deposition with High-Pressure H ₂ O Vapor Heat Treatment. Japanese Journal of Applied Physics, 2012, 51, 03CA06.	1.5	1
41	Carbon Heating Tube Used for Rapid Heating System for Semiconductor Annealing. , 2018, , .		1
42	Passivation of silicon surfaces by heat treatment in boiled water and its application of solar cells. , 2014, , .		0
43	Decrease in reflection loss at intermediate adhesive layer for mechanical stacking multi junction solar cells. , 2014, , .		0
44	Passivation of silicon surfaces by oxygen radical followed by high pressure H ₂ O vapor heat treatments and its application to solar cell fabrication. , 2014, , .		0
45	Annihilation properties of photo-induced carrier in silicon pn junction. , 2015, , .		0
46	Reduction in optical reflection loss at intermediate adhesive layer for mechanical stacked multi-junction solar cells. , 2015, , .		0
47	Microwave rapid heating used for diffusing impurities in silicon. , 2016, , .		0
48	Surface passivation of crystalline silicon by heat treatment in liquid water. , 2016, , .		0
49	Two-Step Ion Implantation used for Activating Boron Atoms in Silicon at 300°C. , 2018, , .		0
50	Surface Passivation of Crystalline Silicon by Heat Treatment in Liquid Water and its Application to Improve the Interface Properties of Metal-Oxide-Semiconductor Structures. , 2018, , .		0
51	Reduction in connecting resistivity and optical reflection loss at intermediate layer for mechanically stacked multijunction solar cells. Japanese Journal of Applied Physics, 2018, 57, 102301.	1.5	0
52	Carbon Heating Tube Rapid Heating System for Fabricating Silicon Solar Cells. , 2019, , .		0
53	Argon Precursor Ion Implantation Used to Activate Boron Atoms in Silicon at Low Temperatures. IEEE Access, 2020, 8, 72598-72606.	4.2	0
54	Activation of 300-mm-Diameter-Phosphorus-Implanted Silicon Substrates by Wireless Carbon Heating Tubes. , 2021, , .		0

#	ARTICLE	IF	CITATIONS
55	Laser Induced Formation of Buried Void Layer in Silicon. Journal of Laser Micro Nanoengineering, 2012, 7, 93-96.	0.1	0
56	Passivation of Silicon Surface by Laser Rapid Heating. Journal of Laser Micro Nanoengineering, 2014, 9, 143-146.	0.1	0
57	Development of Microwave-Induced Rapid Heating System Using Wireless Carbon Heating Tubes. , 2020, , .		0